

CLAIM AMENDMENTS

1. (Currently Amended) A method for burying a resist comprising ~~the steps of:~~
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
~~coating~~ applying a resist film ~~onto~~ to said interlayer film, including said opening; and
patterning said resist film substantially in the same form as said opening, thereby
burying said resist film ~~in the~~ inside of said opening.

2. (Currently Amended) A method for burying a resist comprising ~~the steps of:~~
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
forming ~~another~~ a second film on said interlayer film including said opening;
~~coating~~ applying a resist film ~~on~~ to said ~~another~~ second film; and
patterning said resist film substantially in the same form as said opening, thereby
burying said resist film ~~in the~~ inside of said opening.

3. (Currently Amended) The method for burying a resist according to claim 1,
wherein said resist is ~~made of~~ a positive resist and including patterning said resist ~~is patterned~~
~~by use of~~ with a photomask having a light-shielding portion ~~whose region is smaller in area~~
than said opening.

4. (Currently Amended) The method for burying a resist according to claim 2,
wherein said resist is ~~made of~~ a positive resist and including patterning said resist ~~is patterned~~
~~by use of~~ with a photomask having a light-shielding portion ~~whose region is smaller in area~~
than said opening.

5. (Currently Amended) The method for burying a resist according to claim 1,
wherein said resist is ~~made of~~ a negative resist and including patterning said resist ~~is~~
~~patterned by use of~~ with a photomask having a light-transmitting portion ~~whose region is~~
smaller in area than said opening.

6. (Currently Amended) The method for burying a resist according to claim 2,
wherein said resist is ~~made of~~ a negative resist and including patterning said resist ~~is~~
~~patterned by use of~~ with a photomask having a light-transmitting portion ~~whose region is~~
smaller in area than said opening.

7. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of:~~
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
~~coating~~ applying a resist film ~~on~~ to said interlayer film, including said opening;
patterning said resist film substantially in the same form as said opening, thereby burying said resist film in ~~the inside of~~ said opening; and
etching said interlayer film while masking a bottom portion of said opening with said resist film buried in said opening.

8. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of:~~
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
~~coating another~~ applying a second film on said interlayer film, including said opening;
~~coating~~ applying a resist film on said ~~another~~ second film; and
patterning said resist film substantially in the same form as said opening, thereby burying said resist film in ~~the inside of~~ said opening; and
etching said ~~another~~ second film while masking a bottom portion of said opening with said resist film buried in said opening.